Journal of
Materials Chemistry C

ROYAL SOCIETY
OF CHEMISTRY

CORRECTION

View Article Online
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Cite this: *J. Mater. Chem. C*, 2021, 9, 736

DOI: 10.1039/d0tc90272a

rsc.li/materials-c

Correction: Impact of changes in bond structure on ovonic threshold switching behaviour in $GeSe_2$

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Correction for 'Impact of changes in bond structure on ovonic threshold switching behaviour in $GeSe_2$' by Jonas Keukelier *et al.*, *J. Mater. Chem. C*, 2021, DOI: 10.1039/d0tc04086j.

In the published article, Table 4 contained an error in the row "Adding Sb": the entry "Se–Se↑" should have read "Se–Se↓".

The corrected version of Table 4 is shown below:

Table 4 Summary of the impact of several (post)deposition processes on the bond presence and electrical parameters compared to as-deposited 35% Ge $GeSe_2$. Arrows indicate an increased or decreased presence of bonds

Process	Impact on bonds	Impact on electrical parameters
Annealing	Pure Ge–Ge & Se–Se↓	Lower I_{pris} and higher V_{FF}
	Ge–Se↑	Leaky after FF
Increasing pressure	ETH Ge–Ge↑	Higher I_{pris} and lower V_{FF}
	Ge–Se↓	Minimal impact on V_{th}
Adding Sb	Se–Se↓	Higher I_{pris} and lower V_{FF}
	Se–Sb & Sb–Sb↑	Large variability
Adding N	Ge–Ge & Ge–Se↓	Lower I_{pris} and higher V_{FF}
	Se–Se↑	Leaky after FF
Co-doping Sb + N	Ge–Ge & Se–Se↓	Similar I_{pris} and lower V_{th}
	Sb–N↑	Better stability

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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